

# **isc** Silicon NPN RF Transistor

### **DESCRIPTION**

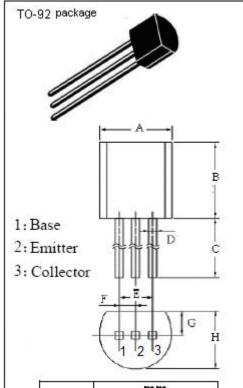
- Low Noise
- High Gain Bandwidth Product
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• Designed for VHF TV tuner and local oscillator applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	19	V
V <sub>EBO</sub>	Emitter-Base Voltage	2	V
Ic	Collector Current-Continuous	50	mA
IE	Emitter Current-Continuous	-50	mA
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	0.3	W
TJ	Junction Temperature 15		°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C



	mm			
DIM	MIN	MAX		
A	4.33	4.83		
В	4.33	4.83		
С	14.0	15.0		
D	0.36	0.56		
Е	2.5	54		
F	1.27			
G	0. 92	1. 12		
н	3.40	3.60		



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2SC1907

#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 10 µ A ; I <sub>E</sub> = 0	30			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 3mA ; R <sub>BE</sub> = ∞	19			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10 μ A ; I <sub>C</sub> = 0	2			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 20mA ; I <sub>B</sub> = 4mA			1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 10V; I <sub>E</sub> = 0			0.5	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 10mA ; V <sub>CE</sub> = 10V	40			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 10mA ; V <sub>CE</sub> = 10V	900	1100		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f= 1.0MHz		1.0	2.0	pF
r <sub>bb'</sub> , • C <sub>C</sub>	Base Time Constant	V <sub>CB</sub> = 10V,I <sub>C</sub> = 10 mA,f = 31.8 MHz		10	25	ps
P <sub>out</sub>	Oscillation Output Power	V <sub>CB</sub> = 10 V,I <sub>C</sub> = 10mA;f = 930MHz		8		mW

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